

APPROVED	O.G. FIG.	
BY	CLASS	SUBCLASS
DRAFTSMAN		

Title: Gallium-Nitride Semiconductor . . . Source Device.  
 Inventor: Toshiyuki OKUMURA  
 Application No.: NEW  
 Docket No.: 204552016410

Fig.1

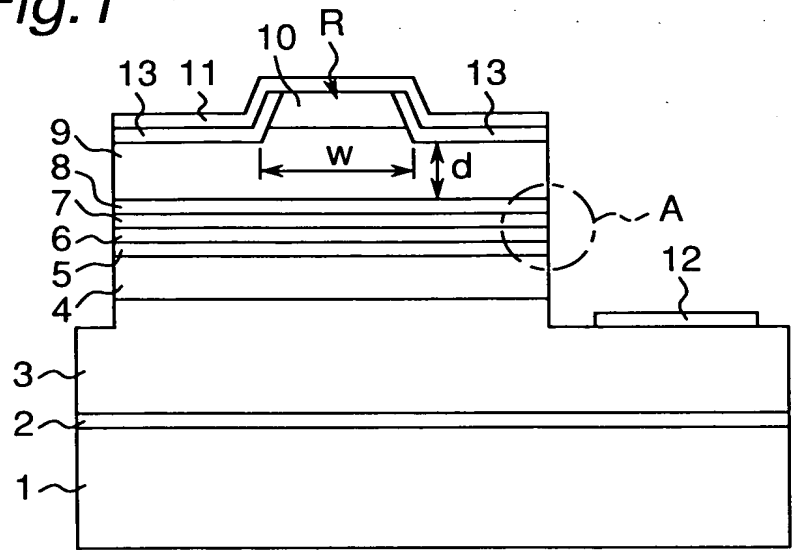


Fig.2

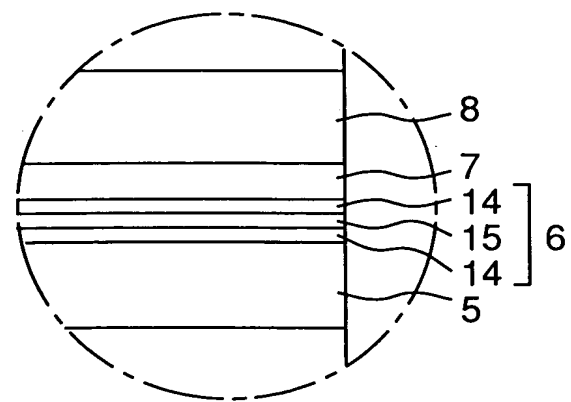


Fig.3

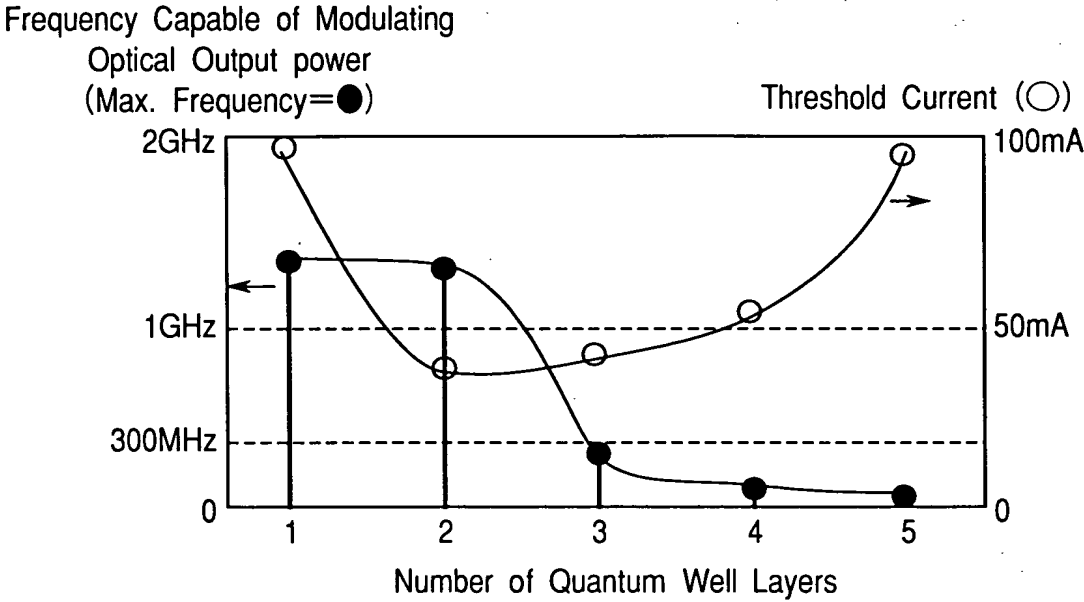


Fig.4

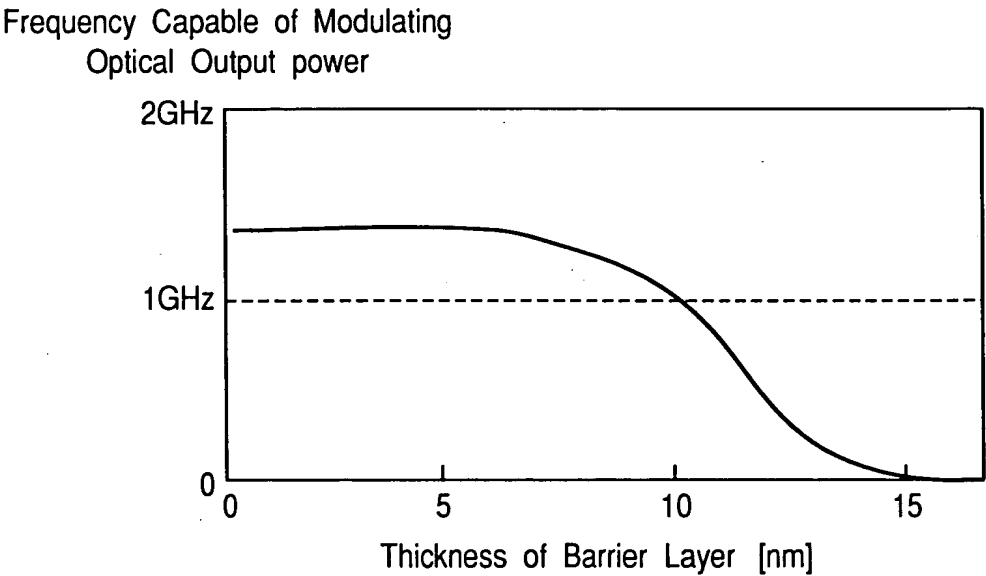


Fig.5

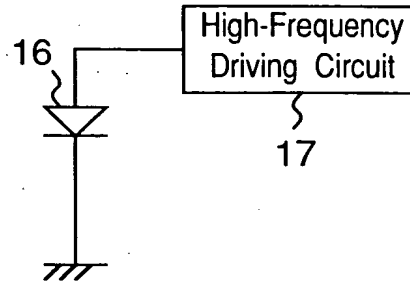


Fig.6

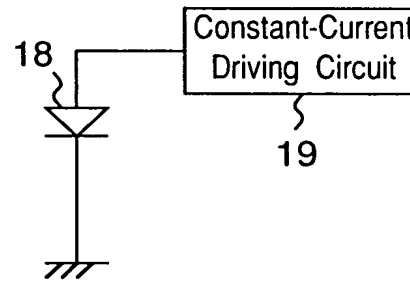
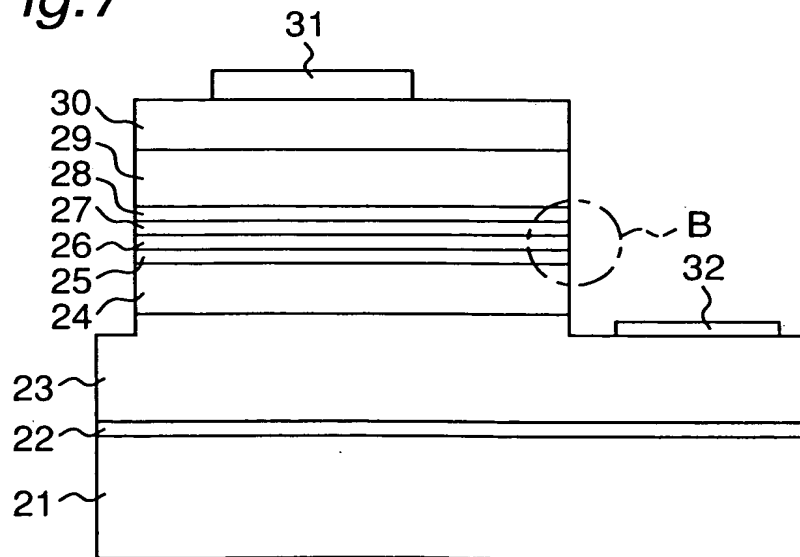


Fig.7



APPROVED	O.C. FIG.
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Fig.8

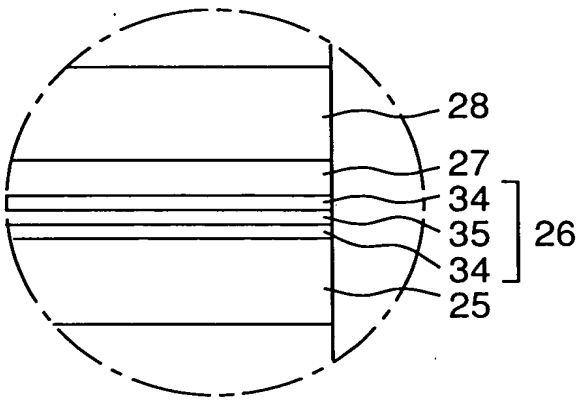
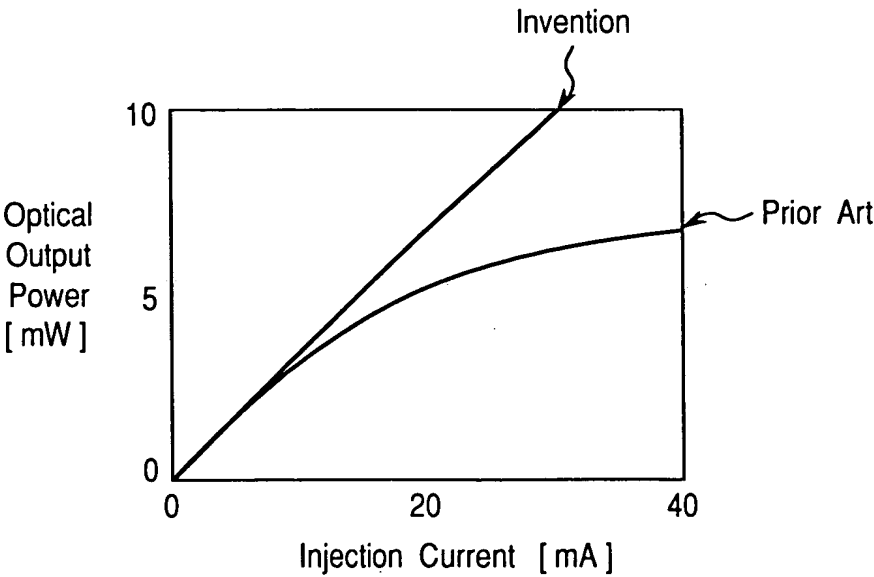


Fig.9



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Fig.10

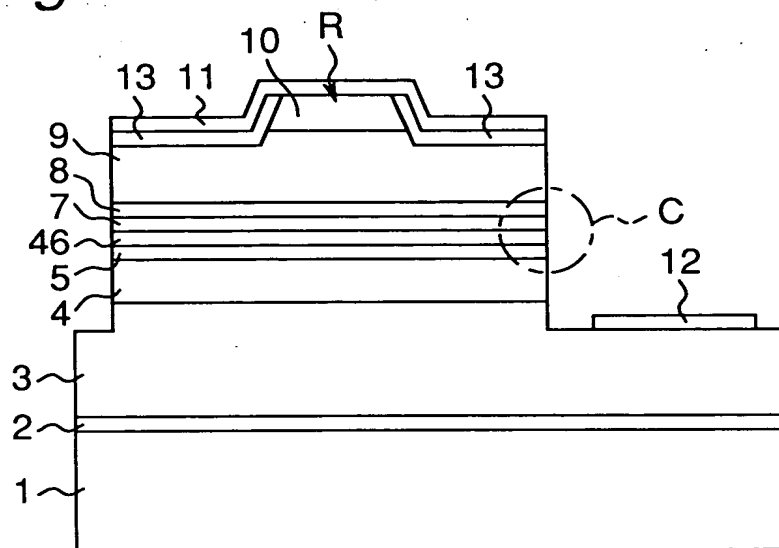
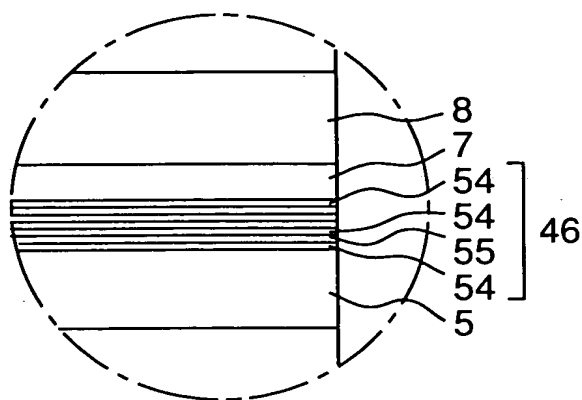


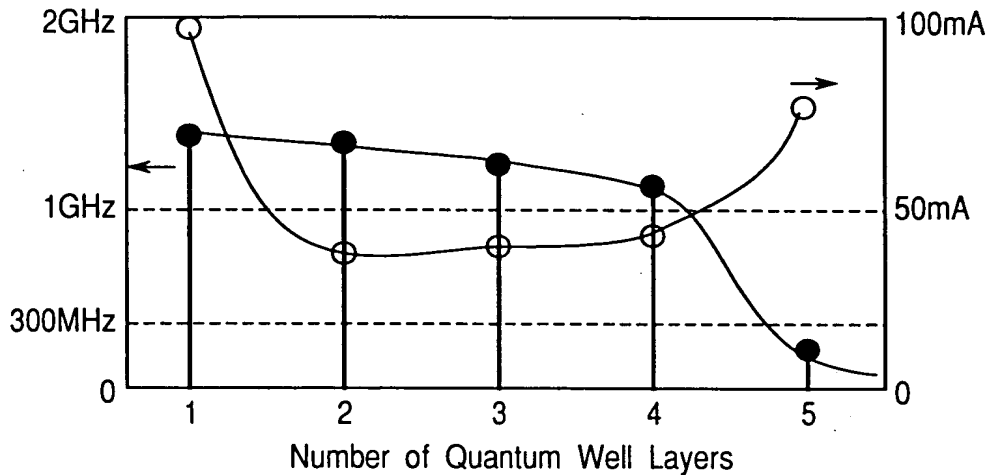
Fig.11



**Fig.12**

Frequency Capable of Modulating  
 Optical Output power  
 (Max. Frequency=●)

Threshold Current (○)



**Fig.13**

Frequency Capable of Modulating  
 Optical Output power

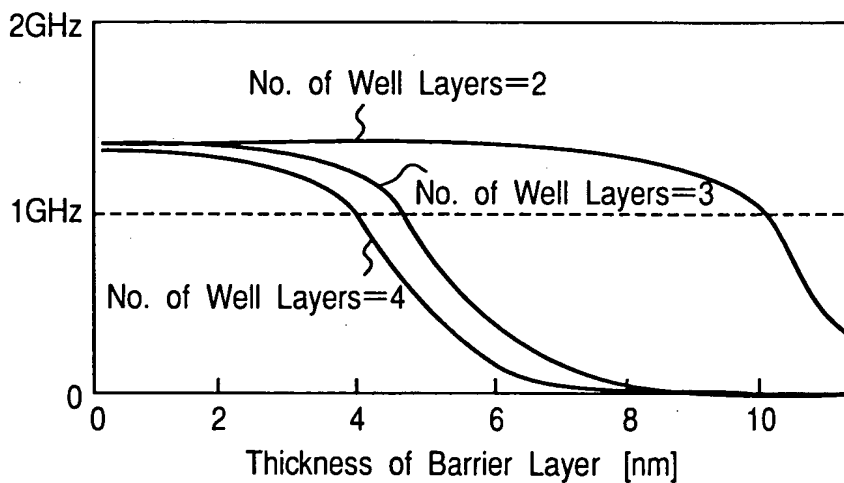


Fig. 14

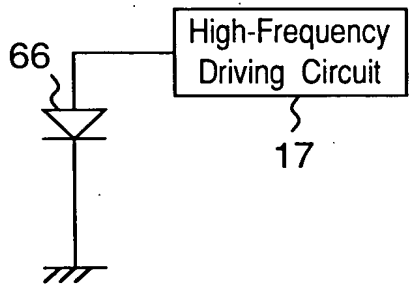


Fig. 15

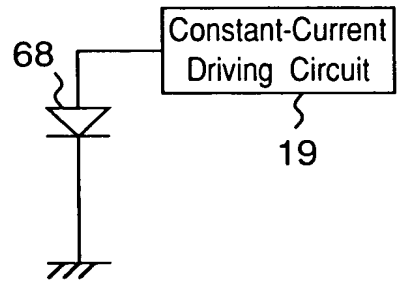


Fig. 16

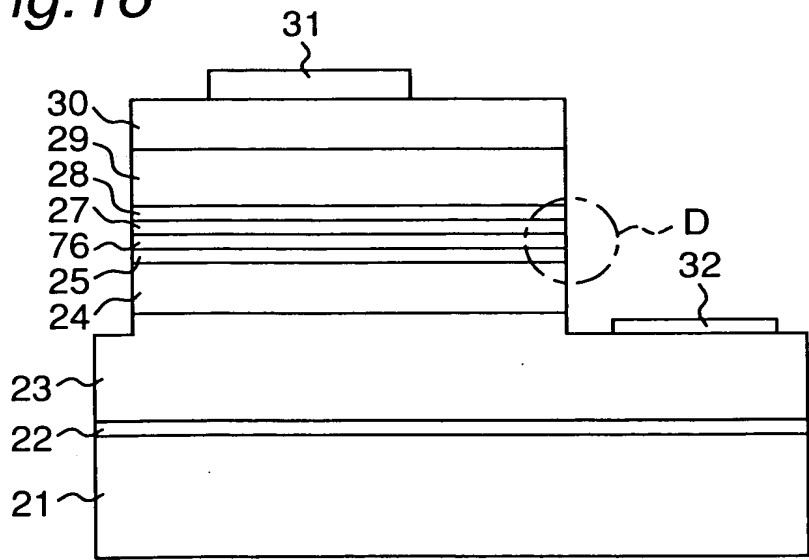


Fig.17

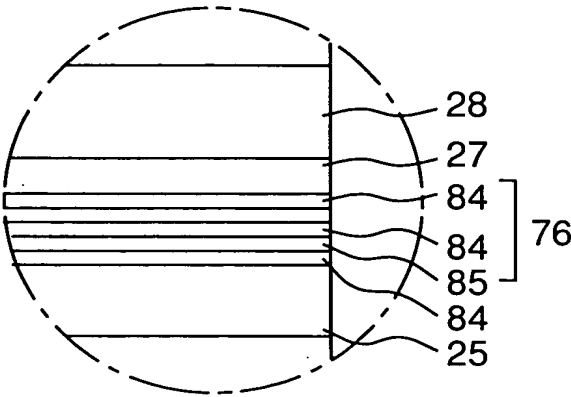


Fig.18

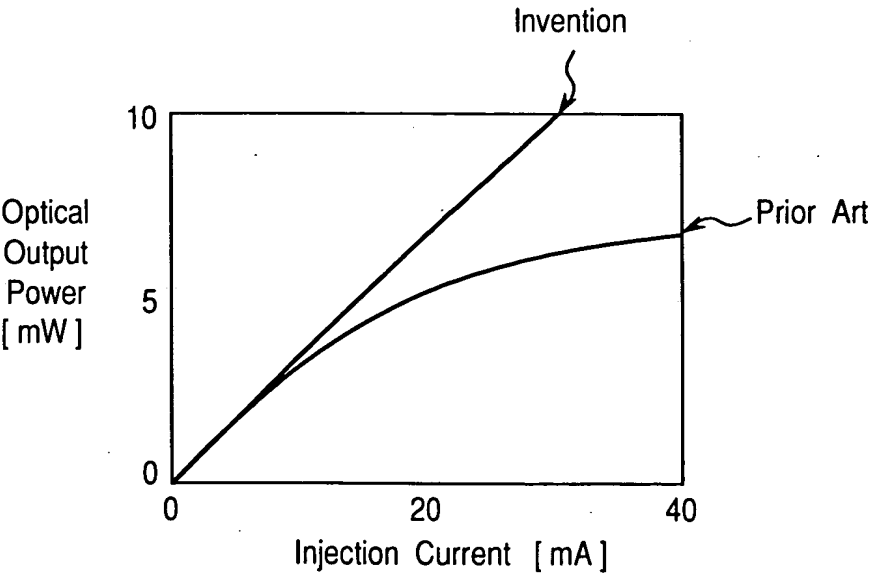




Fig.19

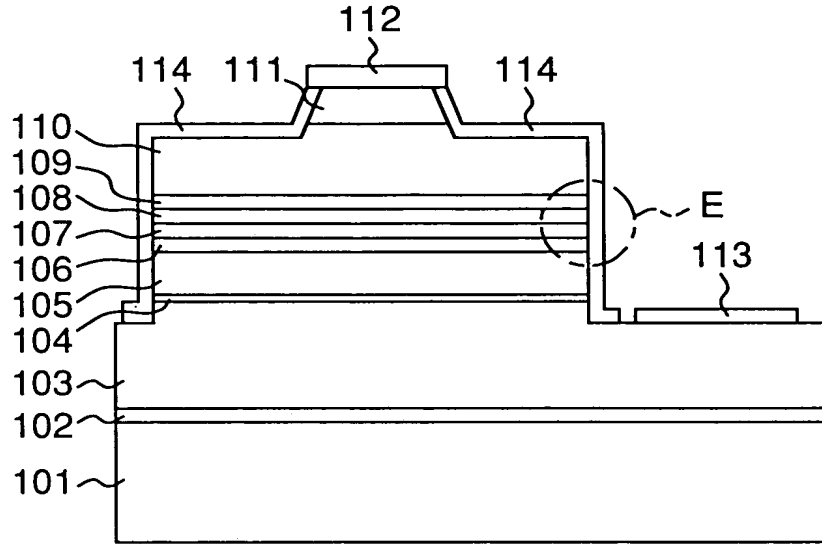
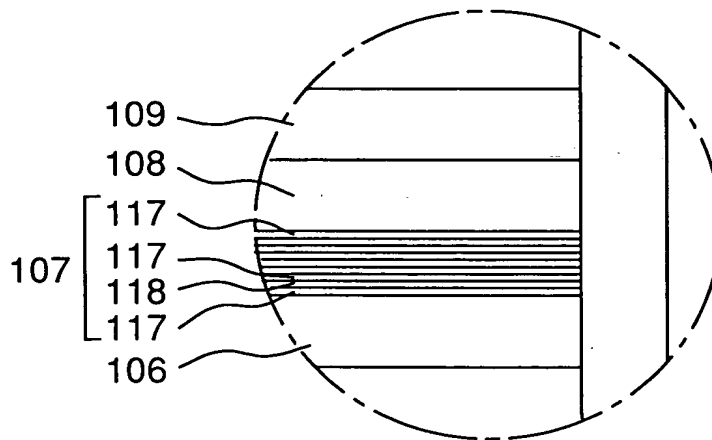


Fig.20



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Fig.21

